



Pro Electron Diode Series

Discrete POWER & Signal Technologies

Leaded Switching Diodes

Device No.	V _{rm} (V) Min	I _{rm} (mA) Min	V _{fm} (V) Max	@	I _f (mA)	t _{tr} (ns) Max	Package No.	Process No.
BAV19	100	100	1		100	50	DO-35	1J (3-13)
BAV20	150	100	1		100	50	DO-35	1J (3-13)
BAV21	200	100	1		100	50	DO-35	1J (3-13)
BAV102	150	100	1		100	50	DO-213AC	1J
BAV103	200	100	1		100	50	DO-213AC	1J
BAW62	75	5000	1		100	4	DO-35	D3
BAW76	50	100	1		100	4	DO-35	D3
BAX13	50	200	1		20	6	DO-35	1R
BAX16	150	100	1.3		100	120	DO-35	1J
BAY19	100	100	1		100	50	DO-35	1J
BAY71	35	100	1		20	4	DO-35	D3
BAY72	100	100	1		100	50	DO-35	1J
BAY73	100	5	1		200	1000	DO-35	1M
BAY80	120	100	1		150	60	DO-35	1J
BAY82	12	100	1		20	0.75	DO-7	1S

NOTE: National preferred device for each process in bold. Number shown in parentheses indicates location (section-page) of device datasheet.